

HSM88WK

Silicon Schottky Barrier Diode for Balanced Mixer

HITACHI

ADE-208-0489F (Z)

Rev 6

Jul 1998

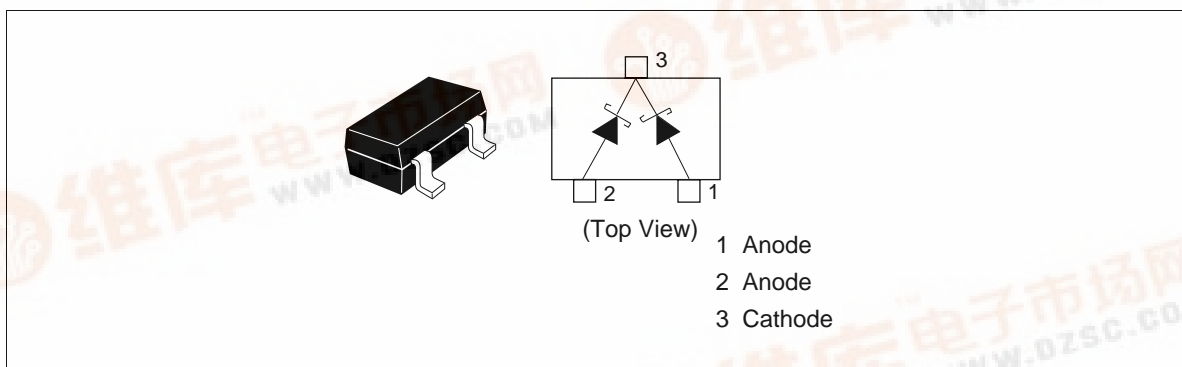
Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM88WK	C4	MPAK

Outline



HSM88WK

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_O^{*1}	15	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Notes 1.Per one device

Electrical Characteristics (Ta = 25°C) ^{*1}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	350	—	420	mV	$I_F = 1 \text{ mA}$
	V_{F2}	500	—	580		$I_F = 10 \text{ mA}$
Reverse current	I_{R1}	—	—	0.2	μA	$V_R = 2 \text{ V}$
	I_{R2}	—	—	10		$V_R = 10 \text{ V}$
Capacitance	C	—	—	0.85	pF	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$
Capacitance deviation	ΔC	—	—	0.10	pF	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$
Forward voltage deviation	ΔV_F	—	—	10	mV	$I_F = 10 \text{ mA}$
ESD-Capability ^{*2}	—	30	—	—	V	C=200pF , Both forward and reverse direction 1 pulse.

Notes 1. Per one device

Notes 2. Failure criterion ; $I_R \geq 400 \text{ nA}$ at $V_R = 2 \text{ V}$

Main Characteristic

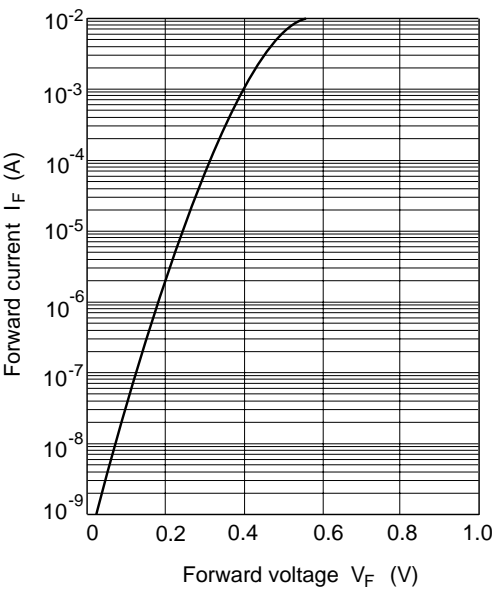


Fig.1 Forward current Vs. Forward voltage

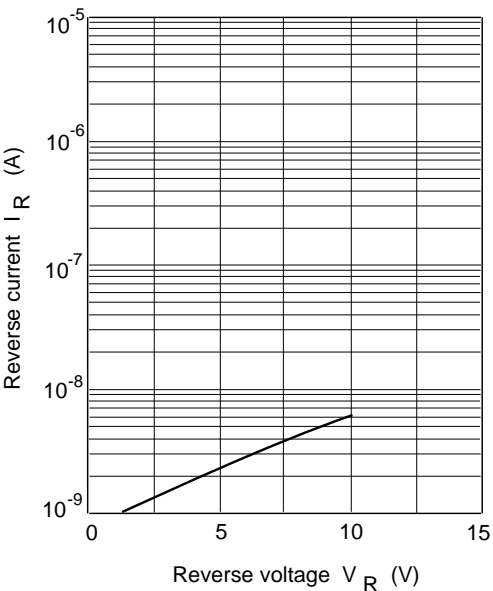


Fig.2 Reverse current Vs. Reverse voltage

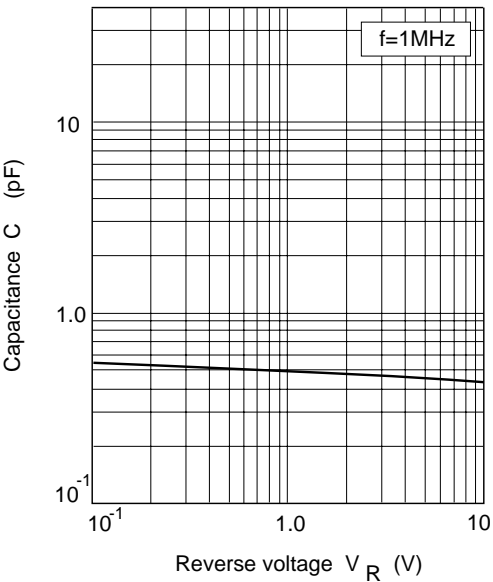
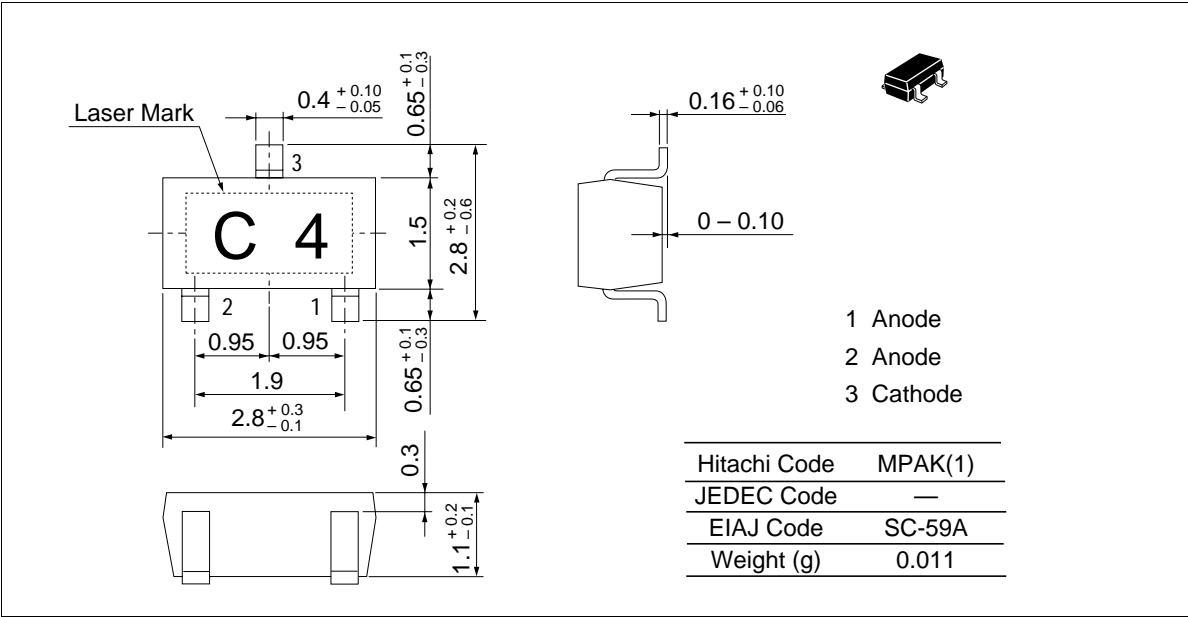


Fig.3 Capacitance Vs. Reverse voltage

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Package Dimensions

Unit : mm



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